



BMS3003 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)1}=5.0m\Omega$ (typ.)
- Input capacitance $C_{iss}=13200pF$ (typ.)
- 4V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-60	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		-78	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-312	A
Allowable Power Dissipation	PD		2.0	W
		$T_c=25^\circ C$	40	W
Channel Temperature	T_{ch}		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	E_{AS}		420	mJ
Avalanche Current *2	I_{AV}		-60	A

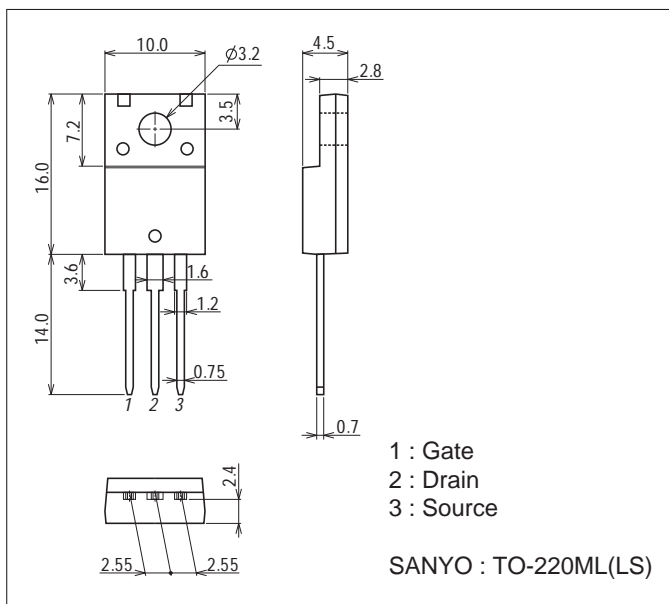
Note : *1 $V_{DD}=-36V$, $L=100\mu H$, $I_{AV}=-60A$ (Fig.1)

*2 $L \leq 100\mu H$, Single pulse

Package Dimensions

unit : mm (typ)

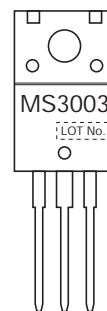
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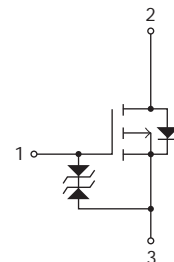
Product & Package Information

- Package : TO-220ML(LS)
- JEITA, JEDEC : SC-67, SOT-186A
- Minimum Packing Quantity : 100 pcs./bag or 50pcs./magazine

Marking



Electrical Connection



BMS3003

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0\text{V}$	-60			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{V}, V_{GS} = 0\text{V}$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{V}, I_D = -39\text{A}$		130		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -39\text{A}, V_{GS} = -10\text{V}$		5.0	6.5	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D = -39\text{A}, V_{GS} = -4\text{V}$		6.5	9.0	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		13200		pF
Output Capacitance	C_{oss}			1300		pF
Reverse Transfer Capacitance	C_{rss}			950		pF
Turn-ON Delay Time	$t_{d(on)}$			90		ns
Rise Time	t_r	See Fig.2		360		ns
Turn-OFF Delay Time	$t_{d(off)}$			1200		ns
Fall Time	t_f			680		ns
Total Gate Charge	Q_g	$V_{DS} = -36\text{V}, V_{GS} = -10\text{V}, I_D = -78\text{A}$		285		nC
Gate-to-Source Charge	Q_{gs}			35		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			70		nC
Diode Forward Voltage	V_{SD}		$I_S = -78\text{A}, V_{GS} = 0\text{V}$	-0.95		-1.5
Reverse Recovery Time	t_{rr}	See Fig.3		150		ns
Reverse Recovery Charge	Q_{rr}	$I_S = -78\text{A}, V_{GS} = 0\text{V}, di/dt = -100\text{A}/\mu\text{s}$		470		nC

Fig.1 Avalanche Resistance Test Circuit

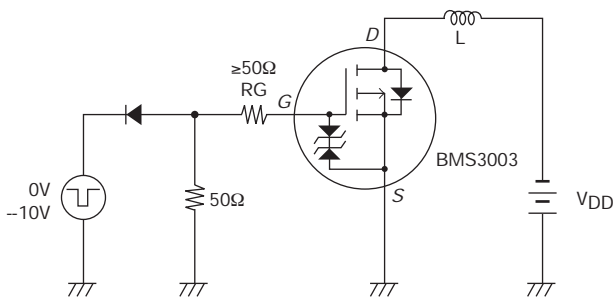


Fig.2 Switching Time Test Circuit

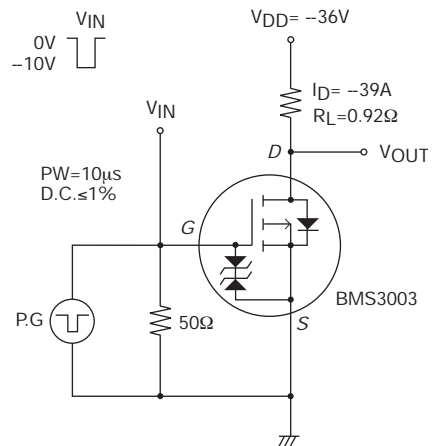
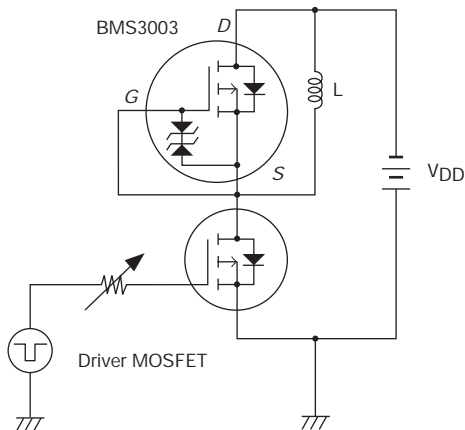
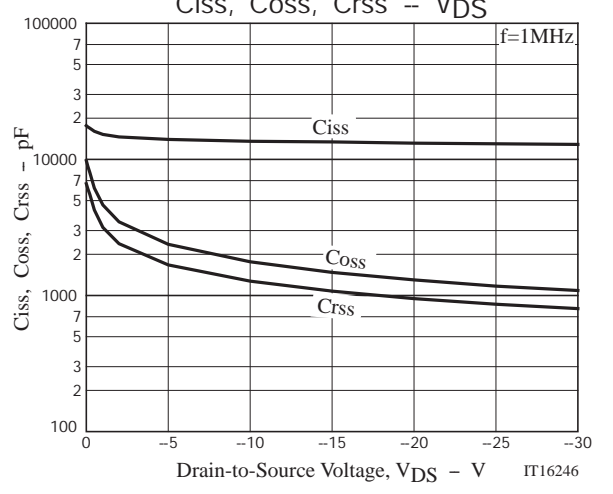
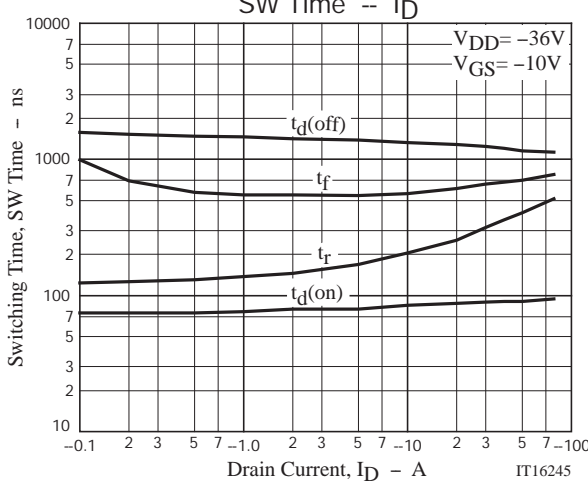
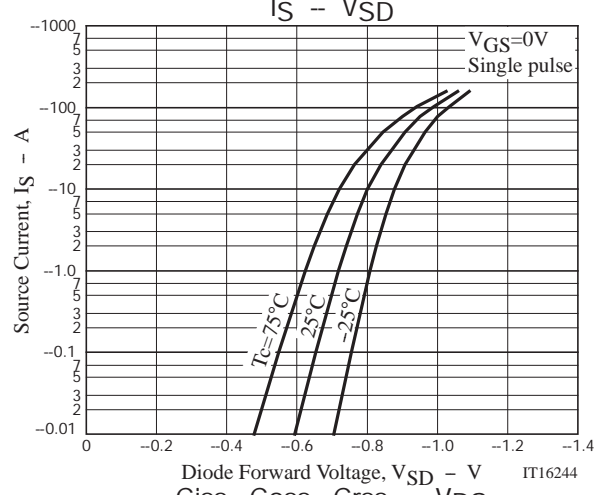
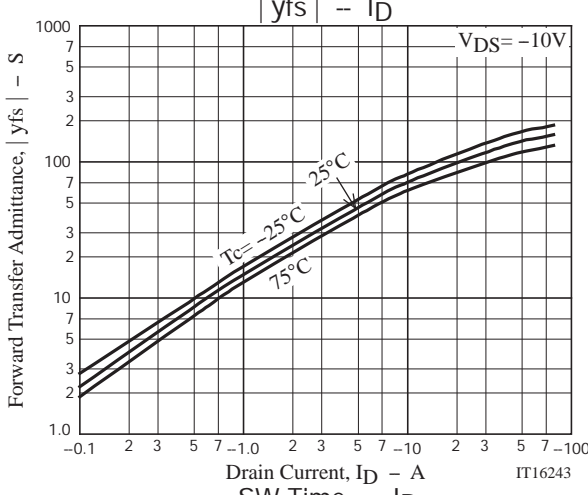
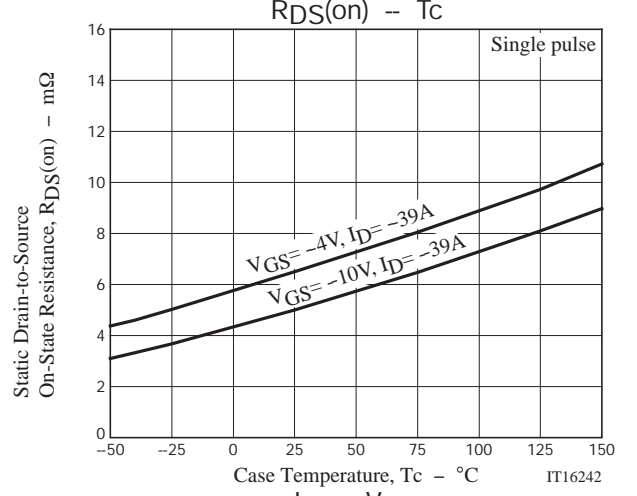
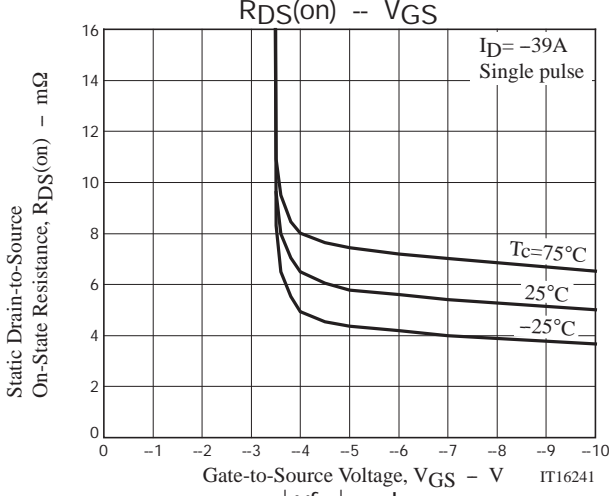
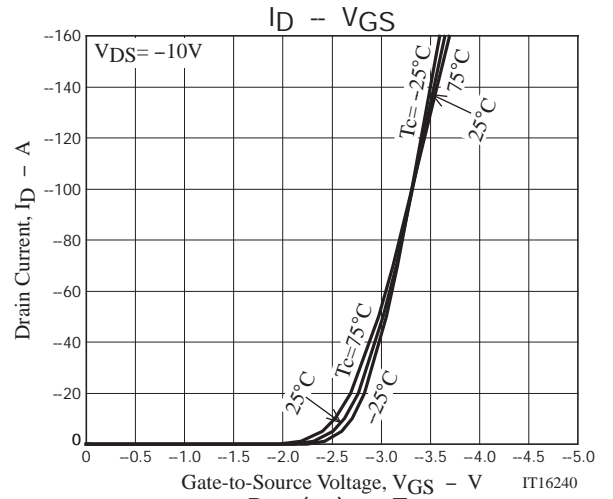
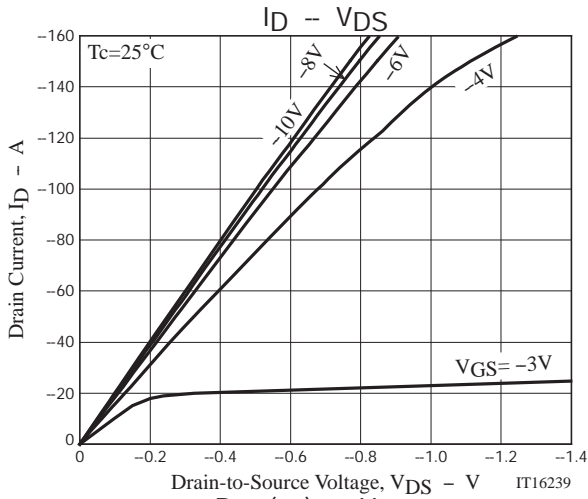
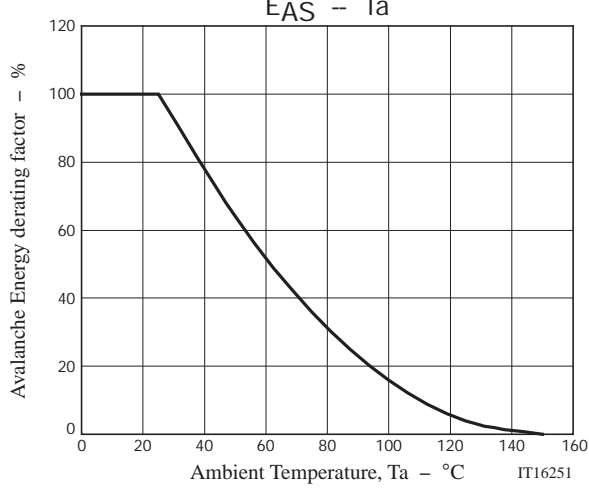
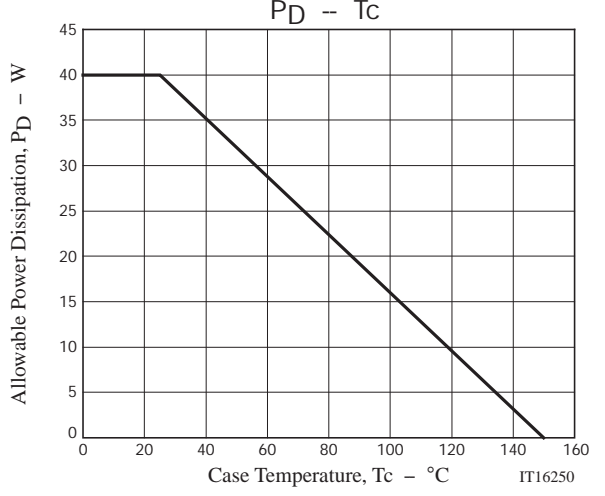
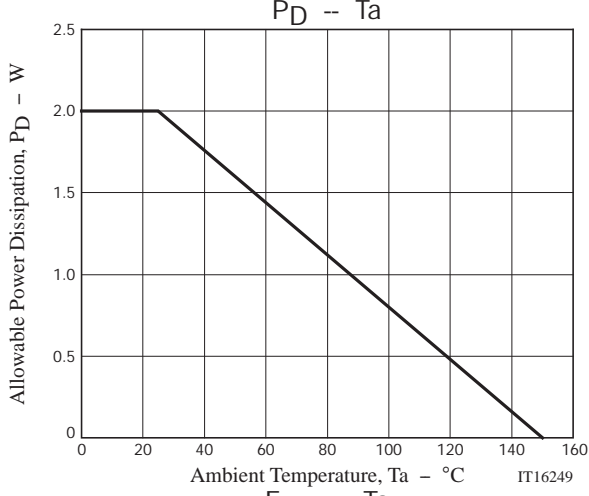
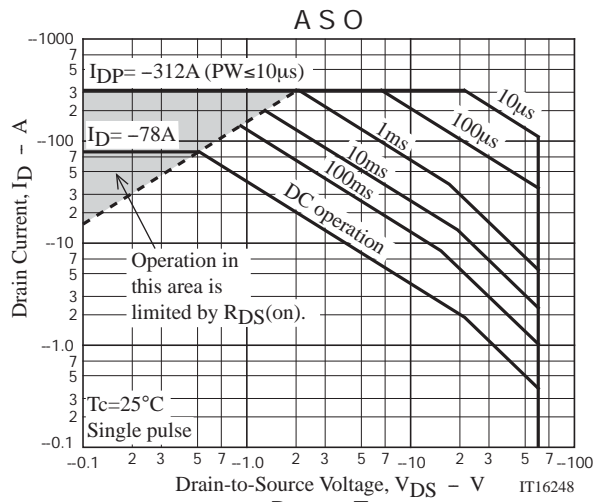
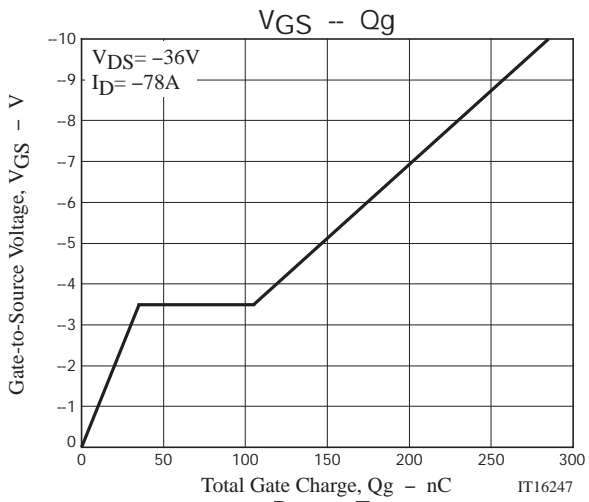


Fig.3 Reverse Recovery Time Test Circuit







Note on usage : Since the BMS3003 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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